International
IOR Rectifier

TARGET

HF40C120ACB

HF40C120ACB Hexfred Die in Wafer Form

1200 V
Size 40
4" Wafer

Electrical Characteristics (Wafer Form)

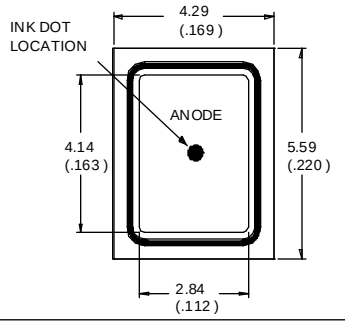
Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	2.6V Max.	T_J = 25°C, I_F = 8.0A
BV_R	Reverse Breakdown Voltage	1200V Min.	T_J = 25°C, I_R = 250µA
I_{RM}	Reverse Leakage Current	20µA Max.	T_J = 25°C, V_R = 1200V

Mechanical Data

Norminal Backmetal Composition, Thickness:	Al-Ti-Ni-Ag (1kA-1kA-4kA-6kA)
Norminal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.169" x 0.220"
Wafer Diameter:	100mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5157
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	See Die Outline drawing below
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA16PB120

Die Outline



NOTES :
1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
2. CONTROLLING DIMENSION : (INCH)
3. LETTER DESIGNATION :
   S = SOURCE SK = SOURCE KELVIN
   G = GATE IS = CURRENT SENSE
4. DIMENSIONAL TOLERANCES
   BONDING PADS : < 0.635 TOLERANCE = +/- 0.013
   WIDTH < (.0250) TOLERANCE =+/- (.0005)
   & > 0.635 TOLERANCE = +/- 0.025
   LENGTH > (.0250) TOLERANCE = +/- (.0010)
   OVERALL DIE < 1.270 TOLERANCE = +/- 0.102
   WIDTH < (.050) TOLERANCE = +/- (.004)
   & > 0.635 TOLERANCE = +/- 0.203
   LENGTH > (.050) TOLERANCE = +/- (.008)
5. UNLESS OTHERWISE NOTED ALL DIE ARE GEN III